Unit: mm

TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process)

2SA970

Low Noise Audio Amplifier Applications

• Low noise: NF = 3dB (typ.) R_G = 100 Ω , V_{CE} = -6 V, I_C = -100 μA , f = 1 kHz : NF = 0.5dB (typ.) R_G = 1 k Ω , V_{CE} = -6 V, I_C = -100 μA , f = 1 kHz

• High DC current gain: $h_{FE} = 200 \sim 700$

• High breakdown voltage: $V_{\rm CEO} = -120 \text{ V}$

• Low pulse noise. Low 1/f noise

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	-120	V
Collector-emitter voltage	V _{CEO}	-120	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _C	-100	mA
Base current	ΙB	-20	mA
Collector power dissipation	PC	300	mW
Junction temperature	Tj	125	°C
Storage temperature range	T _{stg}	-55~125	°C

1. EMITTER 2. COLLECTOR 3. BASE JEDEC TO-92 JEITA SC-43

2-5F1B

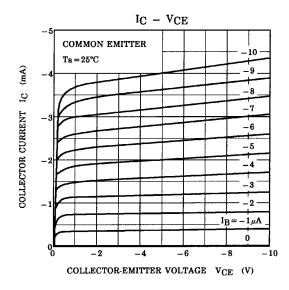
Weight: 0.21 g (typ.)

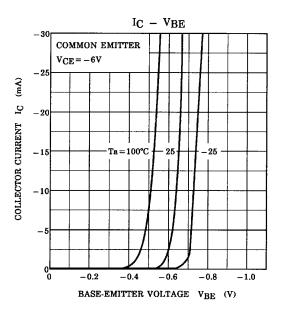
TOSHIBA

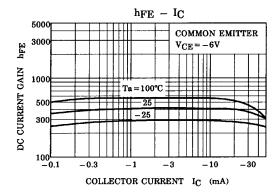
Electrical Characteristics (Ta = 25°C)

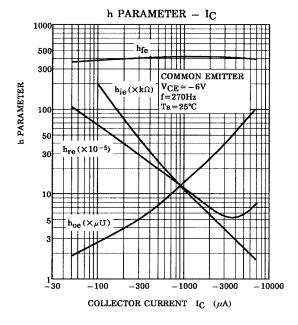
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = -120 \text{ V}, I_E = 0$	_	_	-0.1	μА
Emitter cut-off current	I _{EBO}	$V_{EB} = -5 \text{ V}, I_{C} = 0$	_	_	-0.1	μА
Collector-emitter breakdown voltage	V (BR) CEO	$I_C = -1 \text{ mA}, I_B = 0$	-120	_	_	V
DC current gain	h _{FE} (Note)	$V_{CE} = -6 \text{ V}, I_{C} = -2 \text{ mA}$	200	_	700	
Collector-emitter saturation voltage	V _{CE (sat)}	$I_C = -10 \text{ mA}, I_B = -1 \text{ mA}$	_	_	-0.3	V
Base-emitter voltage	V _{BE}	$V_{CE} = -6 \text{ V}, I_{C} = -2 \text{ mA}$	_	0.65	_	V
Transition frequency	f _T	$V_{CE} = -6 \text{ V}, I_{C} = -1 \text{ mA}$	_	100	_	MHz
Collector output capacitance	C _{ob}	$V_{CB} = -10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$	_	4.0	_	pF
Noise figure NF		$\begin{split} &V_{CE} = -6 \text{ V, I}_{C} = -0.1 \text{ mA, f} = 10 \text{ Hz,} \\ &R_{G} = 10 \text{ k}\Omega \end{split}$	_	_	6	
	NF	$\begin{aligned} &V_{CE} = -6 \text{ V, I}_{C} = -0.1 \text{ mA, f} = 1 \text{ kHz,} \\ &R_{G} = 10 \text{ k}\Omega \end{aligned}$	_	_	2	dB
		$V_{CE} = -6$ V, $I_{C} = -0.1$ mA, $f = 1$ kHz, $R_{G} = 100 \ \Omega$	_	3	_	

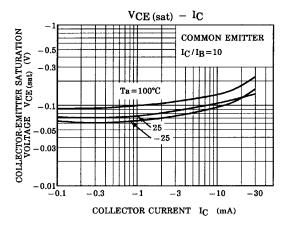
Note: hFE classification GR: 200~400, BL: 350~700



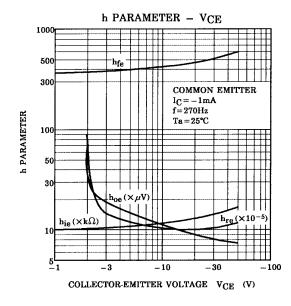


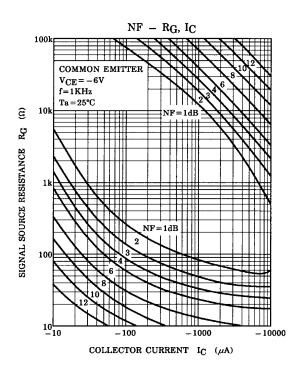


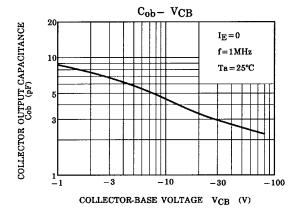


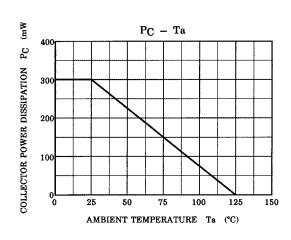


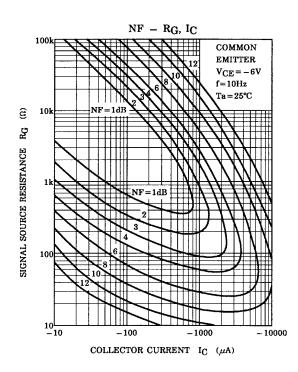
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